

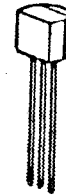
# MICRO ELECTRONICS

**2N5232**

**NPN SILICON  
TRANSISTOR**

2N5232 is NPN silicon planar transistor use in general purpose applications.

TO-92B



ECB

**ABSOLUTE MAXIMUM RATINGS**

Collector-Emitter Voltage	V <sub>CEO</sub>	50V
Collector-Base Voltage	V <sub>CB0</sub>	70V
Emitter-Base Voltage	V <sub>EB0</sub>	5V
Collector Current	I <sub>C</sub>	100mA
Total Power Dissipation	P <sub>tot</sub>	330mW
Operating Junction & Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)**

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	50		V	I <sub>C</sub> =10mA IB=0
Collector-Base Breakdown Voltage	V <sub>CB0</sub>	70		V	I <sub>C</sub> =100µA IE=0
Emitter-Base Breakdown Voltage	V <sub>EB0</sub>	5		V	IE=100µA IC=0
Collector Cutoff Current	I <sub>CB0</sub>		30	nA	V <sub>CB</sub> =50V IE=0
Collector Cutoff Current	I <sub>CS</sub>		30	nA	V <sub>CB</sub> =50V V <sub>EB</sub> =0
Emitter Cutoff Current	I <sub>EB0</sub>		50	nA	V <sub>EB</sub> =5V IC=0
D.C. Current Gain	h <sub>FE</sub>	250	500		I <sub>C</sub> =2mA V <sub>CE</sub> =10V
Base-Emitter Voltage	V <sub>BE</sub>		0.9	V	I <sub>C</sub> =2mA V <sub>CE</sub> =10V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		0.12	V	I <sub>C</sub> =10mA IB=1mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		0.78	V	I <sub>C</sub> =10mA IB=1mA
Output Capacitance	C <sub>ob</sub>		4	pF	V <sub>CB</sub> =10V f=1MHz

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